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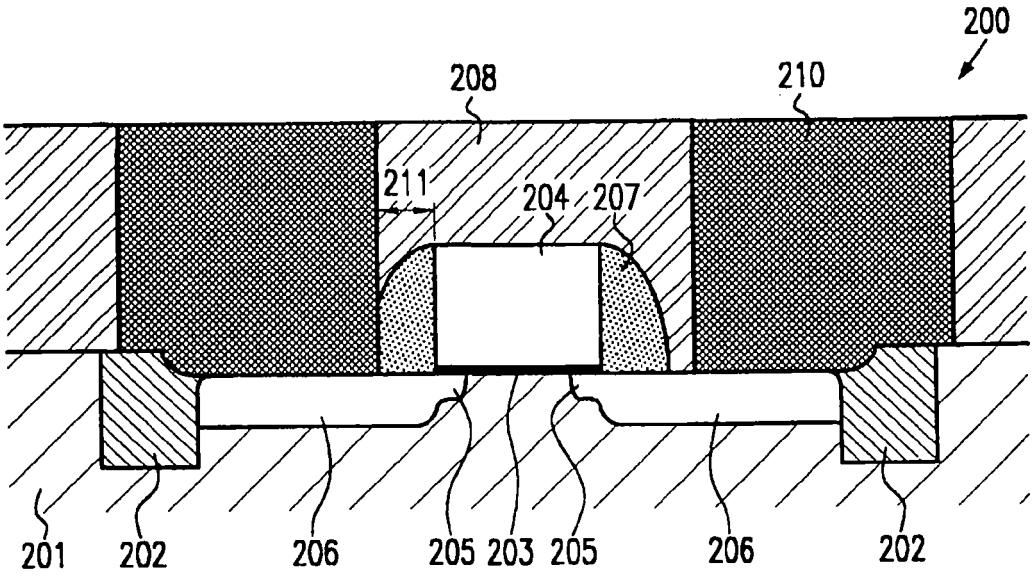
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(54) Title: SEMICONDUCTOR DEVICE WITH REDUCED LINE-TO-LINE CAPACITANCE AND CROSS TALK NOISE



(57) Abstract: A transistor device (200) is disclosed, having an insulating material disposed between the gate electrode (204) and the drain and source lines, wherein the dielectric constant of the insulating amterial is 3.5 or less. Accodingly, the capacitance between the gate electrode and the drain and source lines can be reduced, thereby improving signal performance of the field effect transistor (200) with decreased cross talk noise.

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